TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK2467-Y

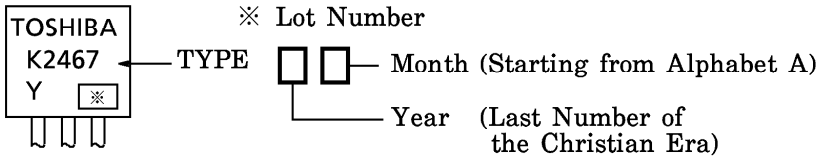
HIGH POWER AMPLIFIER APPLICATION

- High Breakdown Voltage : V_{DSS} = 180V
- High Forward Transfer Admittance : $|Y_{fs}|$ = 4.0S (Typ.)

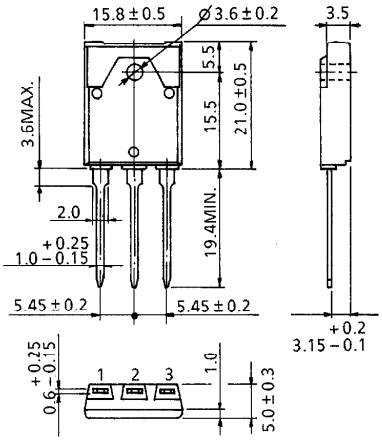
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	180	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current	I_D	9	A
Drain Power Dissipation (Tc = 25°C)	P_D	80	W
Channel Temperature	T_{ch}	150	°C
Storage Temperature Range	T_{stg}	−55~150	°C

MARKING



Unit in mm



1. GATE
2. DRAIN
3. SOURCE

JEDEC	—
EIAJ	—
TOSHIBA	2-16F1B

Weight : 5.8g (Typ.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Drain Cut-Off Current	I_{DSS}	V_{DS} = 180V, V_{GS} = 0	—	—	1.0	mA
Gate Leakage Current	I_{GSS}	V_{DS} = 0, V_{GS} = ±20V	—	—	±0.5	μA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 10mA, V_{GS} = 0	180	—	—	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	V_{GS} = 10V, I_D = 6A	—	2.5	5.0	V
Gate-Source Cut-off Voltage (Note)	$V_{GS(OFF)}$	V_{DS} = 10V, I_D = 0.1A	1.4	—	2.8	V
Forward Transfer Admittance	$\|Y_{fs}\|$	V_{DS} = 10V, I_D = 3A	—	4.0	—	S
Input Capacitance	C_{iss}	V_{DS} = 30V, V_{GS} = 0, f = 1MHz	—	700	—	pF
Output Capacitance	C_{oss}	V_{DS} = 30V, V_{GS} = 0, f = 1MHz	—	150	—	pF
Reverse Capacitance	C_{rss}	V_{DS} = 30V, V_{GS} = 0, f = 1MHz	—	90	—	pF

(Note) : $V_{GS(OFF)}$ Classification Y : 1.4~2.8

This transistor is an electrostatic sensitive device.
Please handle with caution.

961001EAA2

littlediode
COMPONENTS FOR ALL

Littlediode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.